

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device includes a digital circuit part and an analog circuit part that are disposed on a surface of one semiconductor substrate. A dummy layer part made of polysilicon that is the same as polysilicon composing a gate of a transistor is disposed between the digital circuit part and the analog circuit part. The distance between a n-well region in the digital circuit part and a n-well region in the analog circuit part is increased, and a resistance component of the substrate is increased. Accordingly, a parasitic current is drawn from a back gate of the analog circuit part is decreased and the fluctuation of an electric potential is decreased. In addition, a polysilicon layer disposed for adjusting an area ratio of polysilicon to be constant can be utilized as the dummy layer part, thus suppressing an increase of the chip size.